

## N-Channel 200-V (D-S) MOSFET

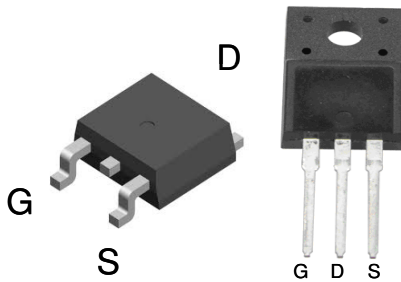
### General Description

B18N20D/F combines advanced trench MOSFET technology with a low resistance package to provide extremely low RDS(ON). This device is ideal for boost converters and synchronous rectifiers for consumer, telecom, industrial power supplies and LED backlighting.

### Features

- $R_{DS(ON)}=180m\Omega@V_{GS}=10V$
- Improved dv/dt capability, high ruggedness
- Exceptional on-resistance and maximum DC current
- TO-252-3/TO-220F-3 Package

### Pin Configuration



### Applications

- LED backlight
- LCD monitor
- LCD TV
- DC/DC Converter
- Load Switch

**Absolute Maximum Ratings** (TA=25°C Unless Otherwise Noted):

Parameter	Symbol	N-Channel	Unit
Drain-Source Voltage	$V_{DSS}$	200	V
Gate-Source Voltage	$V_{GSS}$	±30	V
Continuous Drain Current (tJ=150°C)	$I_D$	TA=25°C	18
		TA=70°C	15
Pulsed Drain Current	$I_{DM}$	60	A
Continuous Source Current (Diode Conduction)	$I_S$	3	A
Maximum Power Dissipation	$P_D$	TA=25°C	83
		TA=70°C	53
Operating Junction Temperature	$T_J$	-55 to 150	°C
Thermal Resistance-Junction to Case	$R_{\theta JC}$	1.5	°C/W